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Contents

xiii Conference Committee

14NM AND BEYOND

- 8683 04 **Computational aspects of optical lithography extension by directed self-assembly** [8683-3]
K. Lai, IBM Corp. (United States); C. Liu, IBM Albany Nano Technology Ctr. (United States); J. Pitera, IBM Almaden Research Ctr. (United States); D. J. Dechene, IBM Corp. (United States); A. Schepis, J. Abdallah, IBM Albany Nano Technology Ctr. (United States); H. Tsai, M. Guillorn, IBM Yorktown Research Ctr. (United States); J. Cheng, G. Doerk, M. Tjio, C. Rettner, IBM Almaden Research Ctr. (United States); O. Odesanya, M. Ozlem, N. Lafferty, IBM Corp. (United States)
- 8683 05 **Sub-12nm optical lithography with 4x pitch division and SMO-lite** [8683-4]
M. C. Smayling, Tela Innovations, Inc. (United States); K. Tsujita, Canon, Inc. (Japan); H. Yaegashi, Tokyo Electron, Ltd. (Japan); V. Axelrad, Sequoia Design Systems, Inc. (United States); T. Arai, Canon, Inc. (Japan); K. Oyama, A. Hara, Tokyo Electron, Ltd. (Japan)
- 8683 06 **Impact of process decisions and alignment strategy on overlay for the 14nm node** [8683-5]
D. Laidler, K. D'havé, P. Leray, J. Hermans, J. Boemmels, S. Cheng, IMEC (Belgium); H. Dai, Y. Chen, B. Mebarki, C. Ngai, Applied Materials, Inc. (United States)
- 8683 07 **The impact of 14-nm photomask uncertainties on computational lithography solutions** [8683-6]
J. Sturtevant, E. Tejnil, T. Lin, S. Schultze, Mentor Graphics Corp. (United States); P. Buck, F. Kalk, K. Nakagawa, Toppan Photomasks, Inc. (United States); G. Ning, P. Ackmann, GLOBALFOUNDRIES Inc. (United States); F. Gans, C. Buergel, Advanced Mask Technology Ctr. (Germany)
- 8683 08 **An investigation into scalability and compliance for triple patterning with stitches for metal 1 at the 14nm node** [8683-7]
C. Cork, Synopsys SARL (France); A. Miloslavsky, P. Friedberg, G. Luk-Pat, Synopsys, Inc. (United States)

SOURCE AND MASK OPTIMIZATION (SMO) I

- 8683 09 **Robust SMO methodology for exposure tool and mask variations in high volume production** [8683-8]
T. Hashimoto, Y. Kai, K. Masukawa, S. Nojima, T. Kotani, Toshiba Corp. (Japan)
- 8683 0A **Imaging application tools for extremely low-k1 ArF immersion lithography** [8683-9]
S. Mori, H. Aoyama, T. Ogata, R. Matsui, T. Matsuyama, Nikon Corp. (Japan)

- 8683 0B **Study of recent CFD-based scheme for analyzing 3D mask effects** [8683-10]
M. Takahashi, K. Kodera, M. Motokubota, Toshiba Corp. (Japan); Y. Kawabata, Toshiba Information Systems Corp. (Japan); S. Maeda, S. Nojima, S. Tanaka, S. Mimotogi, Toshiba Corp. (Japan)
- 8683 0C **The effect of mask and source complexity on source-mask optimization** [8683-11]
S.-H. Yang, N. Jia, S. B. Shim, D. Vengertsev, Y. Kim, J. Choi, H.-K. Kang, Samsung Electronics Co., Ltd. (Korea, Republic of)
- 8683 0D **Illumination pupilgram control using an intelligent illuminator** [8683-12]
N. Hirayanagi, Y. Mizuno, M. Mori, N. Kita, R. Matsui, T. Matsuyama, Nikon Corp. (Japan)

RET

- 8683 0E **Inverse lithography technique for advanced CMOS nodes** [8683-14]
A. Villaret, STMicroelectronics (France); A. Tritchkov, Mentor Graphics Corp. (United States); J. Entradas, Mentor Graphics Ltd. (France); E. Yesilada, STMicroelectronics (France)
- 8683 0F **Mask compensation for process flare in 193nm very low k1 lithography** [8683-15]
J. Lee, T. Lee, S. Oh, C. Kang, J. Kim, J. Choi, C. Park, H. Yang, D. Yim, SK Hynix, Inc. (Korea, Republic of); M. Do, Synopsys, Inc. (Korea, Republic of); I. Su, Synopsys, Inc. (Taiwan); H. Song, Synopsys, Inc. (United States); J.-H. Choi, Synopsys, Inc. (Korea, Republic of); Y. Fan, A. C. Wang, Synopsys, Inc. (United States); S.-W. Lee, Synopsys, Inc. (Korea, Republic of); R. Boone, K. Lucas, Synopsys, Inc. (United States)
- 8683 0G **Pupil waveform manipulation to compensate for mask topography effects in optical nanolithography** [8683-16]
M. Kempsell Sears, B. W. Smith, Rochester Institute of Technology (United States)
- 8683 0H **Effective model-based SRAF placement for full chip 2D layouts** [8683-17]
S. Jayaram, P. LaCour, J. Word, A. Tritchkov, Mentor Graphics Corp. (United States)
- 8683 0I **Wafer topography modeling for ionic implantation mask correction dedicated to 2x nm FDSOI technologies** [8683-18]
J.-C. Michel, J.-C. Le Denmat, E. Sungauer, F. Robert, E. Yesilada, STMicroelectronics (France); A.-M. Armeanu, J. Entradas, Mentor Graphics Ltd. (France); J. L. Sturtevant, T. Do, Y. Granik, Mentor Graphics Corp. (United States)

SOURCE AND MASK OPTIMIZATION (SMO) II

- 8683 0J **Enabling reverse tone imaging for via levels using attenuated phase shift mask and source optimization** [8683-19]
B. Hamieh, STMicroelectronics (United States); H. C. Choi, Samsung Electronics Co., Ltd. (United States); B. Erenturk, GLOBALFOUNDRIES Inc. (United States); W. Guo, IBM Corp. (United States); A. Hamouda, H. Liu, GLOBALFOUNDRIES Inc. (United States); G. McIntyre, J. Meiring, IBM Corp. (United States); D. Moreau, STMicroelectronics (United States); A. Thomas, A. Wei, IBM Corp. (United States)

- 8683 0K **Introducing a novel flow to estimate challenges encountered while transitioning from RET development to manufacturable solution** [8683-20]
J. Cheng, GLOBALFOUNDRIES Inc. (Singapore); R. Chia, Mentor Graphics Corp. (United States); Y. Gong, GLOBALFOUNDRIES Inc. (Singapore); O. ElSewefy, Mentor Graphics Corp. (United States); G. S. Chua, Y. M. Foong, GLOBALFOUNDRIES Inc. (Singapore); A. Dave, A. Chua, Mentor Graphics Corp. (United States); D. Q. Zhang, GLOBALFOUNDRIES Inc. (Singapore); V. Liubich, P. Lacour, A. Tritchkov, Mentor Graphics Corp. (United States)
- 8683 0L **Manufacturability of computation lithography mask: current limit and requirements for sub-20nm node** [8683-21]
J. Choi, I.-Y. Kang, J. S. Park, I. K. Shin, C.-U. Jeon, Samsung Electronics Co., Ltd. (Korea, Republic of)
- 8683 0M **The impact of realistic source shape and flexibility on source mask optimization** [8683-22]
H. Aoyama, Y. Mizuno, N. Hirayanagi, N. Kita, R. Matsui, Nikon Corp. (Japan); H. Izumi, K. Tajima, Nihon Synopsis G. K. (Japan); J. Siebert, W. Demmerle, Synopsis GmbH (Germany); T. Matsuyama, Nikon Corp. (Japan)
- 8683 0N **Source and mask optimization to mitigate hotspots in etch process** [8683-23]
Y. Kono, Y. Kai, K. Masukawa, S. Tamaoki, T. Hashimoto, T. Kimura, R. Aburada, T. Kotani, Toshiba Corp. (Japan)
- 8683 0O **Global source optimization for MEEF and OPE** [8683-24]
R. Matsui, T. Noda, H. Aoyama, N. Kita, T. Matsuyama, Nikon Corp. (Japan); D. Flagello, Nikon Research Corp. of America (United States)

PROCESS TECHNOLOGY I

- 8683 0P **Integrated scatterometry for tight overlay and CD control to enable 20-nm node wafer manufacturing.** [8683-25]
J. Benschop, A. Engelen, H. Cramer, M. Kubis, P. Hinnen, H. van der Laan, K. Bhattacharyya, J. Mulkens, ASML Netherlands B.V. (Netherlands)
- 8683 0Q **Mix-and-match overlay performance of the NSR-S622D immersion scanner** [8683-26]
K. Makino, T. Kikuchi, S. Sasamoto, P. Hongki, A. Mori, N. Takahashi, S. Wakamoto, Nikon Corp. (Japan)
- 8683 0R **Lithographic challenges and their solutions for critical layers in sub-14nm node logic devices** [8683-92]
T.-B. Chiou, ASML (Taiwan); M. Dusa, ASML (Belgium); A. C. Chen, ASML (Taiwan); D. Pietromonaco, ARM Ltd. (United States)
- 8683 0S **Lithography imaging control by enhanced monitoring of light source performance** [8683-28]
P. Alagna, Cymer, Inc. (United States) and Cymer, Inc. (Belgium); O. Zurita, I. Lalovic, N. Seong, G. Rechsteiner, J. Thornes, Cymer, Inc. (Belgium); K. D'havé, L. Van Look, J. Bekaert, IMEC (Belgium)

MODELING

- 8683 0U **Solutions with precise prediction for thermal aberration error in low-k1 immersion lithography** [8683-29]
K. Fukuhara, A. Mimotogi, T. Kono, Toshiba Corp. (Japan); H. Aoyama, T. Ogata, N. Kita, T. Matsuyama, Nikon Corp. (Japan)
- 8683 0V **Compact OPC model optimization using emulated data** [8683-30]
A. Isoyan, Synopsys, Inc. (United States); T. Mülders, Synopsys GmbH (Germany); C. Westwood, L. S. Melvin III, Synopsys, Inc. (United States)
- 8683 0W **A study on the automation of scanner matching** [8683-31]
Y. He, Micron Technology, Inc. (United States); A. Serebryakov, ASML US, Inc. (United States); S. Light, Micron Technology, Inc. (United States); V. Jain, ASML US, Inc. (United States); E. Byers, Micron Technology, Inc. (United States); R. Goossens, Z.-Y. Niu, P. Engblom, S. Larson, ASML US, Inc. (United States); B. Geh, Carl Zeiss SMT Inc. (United States); C. Hickman, H. Kang, Micron Technology, Inc. (United States)
- 8683 0X **Adjustment of image decomposition mode and reflection criterion focusing on critical dimension uniformity and exposure dose effectiveness under diffraction effects in optical microlithography using a digital micromirror device** [8683-32]
M. Seo, H. Kim, Tongmyong Univ. (Korea, Republic of)
- 8683 0Y **Simulation of spacer-based SADP (Self-Aligned Double-Patterning) for 15nm half pitch** [8683-33]
S. Robertson, KLA-Tencor Texas (United States); P. Wong, J. Versluijs, V. Wiaux, IMEC (Belgium)

PROCESS TECHNOLOGY II

- 8683 0Z **A comparative study of self-aligned quadruple and sextuple patterning techniques for sub-15nm IC scaling** [8683-34]
Y. Chen, W. Kang, P. Zhang, Peking Univ. (China)
- 8683 10 **Grayscale lithography: 3D structuring and thickness control** [8683-35]
M. Heller, D. Kaiser, M. Stegemann, G. Holfeld, N. Morgana, J. Schneider, D. Sarlette, Infineon Technologies Dresden GmbH (Germany)
- 8683 11 **Sidewall profile inclination modulation mask (SPIMM): modification of an attenuated phase-shift mask for single-exposure double and multiple patterning** [8683-36]
F. T. Chen, W.-S. Chen, M.-J. Tsai, T.-K. Ku, Industrial Technology Research Institute (Taiwan)
- 8683 12 **Avoiding wafer-print artifacts in spacer is dielectric (SID) patterning** [8683-37]
G. Luk-Pat, B. Painter, A. Miloslavsky, Synopsys, Inc. (United States); P. De Bisschop, IMEC (Belgium); A. Beacham, Synopsys, Inc. (Canada); K. Lucas, Synopsys, Inc. (United States)
- 8683 13 **Best focus shift mitigation for extending the depth of focus** [8683-38]
A. Szucs, J. Planchot, V. Farys, E. Yesilada, C. Alleaume, STMicroelectronics (France); L. Depre, R. Dover, ASML Brion (United States); C. Gourgon, M. Besacier, LTM, CNRS, CEA (France); A. Nachtwein, P. Rusu, ASML Nederland B.V. (Netherlands)

- 8683 14 **Wafer sub-layer impact in OPC/ORC models for 2x nm node implant layers** [8683-39]
J.-C. Le-Denmat, C. Martinelli, E. Sungauer, J.-C. Michel, E. Yesilada, F. Robert,
STMicroelectronics (France)

OPTICAL AND DFM I: JOINT SESSION WITH CONFERENCES 8683 AND 8684

- 8683 15 **Interference harmonics and rigorous EM spectrum analysis method for low-k1 CD Bossung tilt correction** [8683-40]
S.-Y. Chou, H.-T. Ng, Y.-Y. Chen, C.-F. Lee, R.-G. Liu, T.-S. Gau, Taiwan Semiconductor Manufacturing Co. Ltd. (Taiwan)
- 8683 16 **Model based stitching and inter-mask bridge prevention for double patterning lithography** [8683-41]
G. Landié, J.-N. Pena, STMicroelectronics (France); S. Postnikov, Mentor Graphics Corp. (France); J. Word, S. Shang, Mentor Graphics Corp. (United States); F. Chaoui, Mentor Graphics Corp. (France); E. Yesilada, C. Martinelli, STMicroelectronics (France)
- 8683 17 **Application of artificial neural networks to compact mask models in optical lithography simulation (Best Student Paper Award)** [8683-42]
V. Agudelo, Friedrich-Alexander-Univ. Erlangen-Nürnberg (Germany) and Fraunhofer-Institut für Integrierte Systeme und Bauelementetechnologie (Germany); T. Fühner, Fraunhofer-Institut für Integrierte Systeme und Bauelementetechnologie (Germany); A. Erdmann, Friedrich-Alexander-Univ. Erlangen-Nürnberg (Germany) and Fraunhofer-Institut für Integrierte Systeme und Bauelementetechnologie (Germany); P. Evanschitzky, Fraunhofer-Institut für Integrierte Systeme und Bauelementetechnologie (Germany)

OPTICAL AND DFM II: JOINT SESSION WITH CONFERENCES 8683 AND 8684

- 8683 18 **3D resist profile modeling for OPC applications** [8683-43]
Y. Fan, Synopsys, Inc. (United States); K. K. Koh, Q. Yang, GLOBALFOUNDRIES Inc. (Singapore); W. Hoppe, B. Kuechler, Synopsys GmbH (Germany); P. Perampalam, M. Miyagi, L. Zavyalova, Synopsys, Inc. (United States); T. Schmöller, Synopsys GmbH (Germany)
- 8683 19 **On the accuracy of different Fourier transforms of VLSI designs** [8683-44]
R. Nasser, P. Hurley, IBM Zürich Research Lab (Switzerland)

SIMULATION

- 8683 1A **Benchmarking study of 3D mask modeling for 2X and 1X nodes** [8683-45]
C. A. Wang, C.-C. Liang, H. Liu, C. Kallingal, GLOBALFOUNDRIES Inc. (United States); D. Dunn, J. Oberschmidt, IBM Corp. (United States); J. Tirapu Azpiroz, IBM Corp. (Brazil)
- 8683 1B **OPC resist model separability validation after SMO source change** [8683-46]
W. Gillijns, J. Van de Kerkhove, D. Trivkovic, P. De Bisschop, IMEC (Belgium); D. Rio, S. Hsu, M. Feng, Q. Zhang, H. Liu, ASML Brion (United States)

- 8683 1C **Topographic mask modeling with reduced basis finite element method** [8683-47]
J. K. Tyminski, Nikon Research Corp. of America (United States); J. Pomplun, L. Zschiedrich, JCMwave GmbH (Germany); D. Flagello, Nikon Research Corp. of America (United States); T. Matsuyama, Nikon Corp. (Japan)
- 8683 1D **Accurate 3DEM^F mask model for full-chip simulation** [8683-48]
M. C. Lam, K. Adam, D. Fryer, C. Zuniga, H. Wei, M. Oliver, C. H. Clifford, Mentor Graphics Corp. (United States)
- 8683 1E **Role of 3D photo-resist simulation for advanced technology nodes** [8683-49]
A. Narayana Samy, R. Seltmann, F. Kahlenberg, J. Schramm, GLOBALFOUNDRIES Inc. (Germany); B. Küchler, U. Klostermann, Synopsys GmbH (Germany)

TOOLING

- 8683 1F **A study of vertical lithography for high-density 3D structures** [8683-50]
M. Mizutani, S.-I. Hirai, I. Koizumi, K.-I. Mori, S. Miura, Canon Inc. (Japan)
- 8683 1G **Power up: 120 Watt injection-locked ArF excimer laser required for both multi-patterning and 450 mm wafer lithography** [8683-51]
T. Asayama, Y. Sasaki, T. Nagashima, A. Kurosu, H. Tsushima, T. Kumazaki, K. Kakizaki, T. Matsunaga, H. Mizoguchi, Gigaphoton Inc. (Japan)
- 8683 1H **High power 120W ArF immersion XLR laser system for high dose applications** [8683-52]
R. Rokitski, R. Rafac, J. Melchior, R. Dubi, J. Thornes, T. Cacouris, M. Haviland, D. Brown, Cymer, Inc. (United States)
- 8683 1I **Comprehensive thermal aberration and distortion control of lithographic lenses for accurate overlay** [8683-53]
Y. Fujishima, S. Ishiyama, S. Isago, A. Fukui, H. Yamamoto, T. Hirayama, T. Matsuyama, Y. Ohmura, Nikon Corp. (Japan)
- 8683 1J **High order field-to-field corrections for imaging and overlay to achieve sub 20-nm lithography requirements** [8683-54]
J. Mulkens, M. Kubis, P. Hinnen, R. de Graaf, H. van der Laan, A. Padiy, B. Menchtchikov, ASML Netherlands B.V. (Netherlands)
- 8683 1K **High-productivity immersion scanner enabling 1xnm hp manufacturing** [8683-55]
Y. Shirata, Y. Shibasaki, J. Kosugi, T. Kikuchi, Y. Ohmura, Nikon Corp. (Japan)
- 8683 1L **Extending immersion lithography down to 1x nm production nodes** [8683-91]
W. de Boeij, R. Pieterella, I. Bouchoms, M. Leenders, M. Hoofman, R. de Graaf, H. Kok, P. Broman, J. Smits, J.-J. Kuit, M. McLaren, ASML Netherlands B.V. (Netherlands)

POSTER SESSION

- 8683 1M **Compatibility of optimized source over design changes in the foundry environment** [8683-56]
J. Pei, Semiconductor Manufacturing International Corp. (China); F. Shao, O. ElSewefy, C. Zhu, Mentor Graphics Corp. (United States); V. Xu, Semiconductor Manufacturing International Corp. (China); Y. Zhu, L. Zhang, Mentor Graphics Corp. (United States); X. Shi, Q. Liu, Semiconductor Manufacturing International Corp. (China); A. Dave, Mentor Graphics Corp. (United States)
- 8683 1N **3D resist profile full chip verification and hot spot disposition** [8683-57]
Q. Yang, S. F. Quek, Y. M. Foong, GLOBALFOUNDRIES Inc. (Singapore); J. Hassmann, GLOBALFOUNDRIES Inc. (Germany); D. Zhang, GLOBALFOUNDRIES Inc. (Singapore); A. Leschok, GLOBALFOUNDRIES Inc. (Germany); T. Yun, GLOBALFOUNDRIES Inc. (Singapore); M. Feng, S. Baron, J. H. Qiu, T. Pandey, B. Yan, R. Dover, ASML Brion Technologies (United States)
- 8683 1P **3D lithography for implant applications** [8683-59]
J. Schneider, H. Feick, D. Kaiser, M. Heller, D. Sarlette, Infineon Technologies Dresden GmbH (Germany)
- 8683 1Q **Lens heating impact analysis and controls for critical device layers by computational method** [8683-60]
D. H. Beak, J. P. Choi, T. Park, Y. S. Nam, Y. S. Kang, C. H. Park, Samsung Electronics Co., Ltd. (Korea, Republic of); K.-Y. Park, C.-H. Ryu, W. Huang, K.-H. Baik, ASML Korea Co., Ltd. (Korea, Republic of)
- 8683 1R **Effects of focus difference of nested and isolated features for scanner proximity matching** [8683-61]
G. Ning, GLOBALFOUNDRIES Inc. (United States); and GLOBALFOUNDRIES Inc. (Germany); P. Ackmann, H. Koh, GLOBALFOUNDRIES Inc. (United States); F. Richter, M. Ruhm, J. Busch, GLOBALFOUNDRIES Inc. (Germany); N. Chen, GLOBALFOUNDRIES Inc. (United States); K. Kurth, A. Leschok, GLOBALFOUNDRIES Inc. (Germany); C. T. Lim, GLOBALFOUNDRIES Inc. (United States)
- 8683 1T **Source mask optimization using real-coded genetic algorithms** [8683-63]
C. Yang, X. Wang, S. Li, Shanghai Institute of Optics and Fine Mechanics (China) and Graduate School of the Chinese Academy of Sciences (China); A. Erdmann, Fraunhofer-Institut für Integrierte Systeme und Bauelementetechnologie (Germany)
- 8683 1V **Mask 3D effects on contact layouts of 1Xnm NAND flash devices** [8683-65]
J. Jang, H. Jeong, H. Yune, S. Oh, H. Yang, D. Yim, SK Hynix, Inc. (Korea, Republic of)
- 8683 1W **High speed and flexible PEB 3D diffusion simulation based on Sylvester equation** [8683-66]
P.-C. Lin, C. C-P. Chen, National Taiwan Univ. (Taiwan)
- 8683 1Y **Line edge roughness (LER) mitigation studies specific to interference-like lithography** [8683-68]
B. Baylav, A. Estroff, Rochester Institute of Technology (United States); P. Xie, Applied Materials, Inc. (United States); B. W. Smith, Rochester Institute of Technology (United States)

- 8683 1Z **The studies of SMO process on cont layer of 20nm node** [8683-69]
W. C. Lo, Y. F. Cheng, M. J. Chen, United Microelectronics Corp. (Taiwan)
- 8683 22 **SMO and NTD for robust single exposure solution on contact patterning for 40nm node flash memory devices** [8683-72]
C.-C. Yu, C. C. Yang, E. Yang, T. H. Yang, K. C. Chen, C.-Y. Lu, Macronix International Co., Ltd. (Taiwan)
- 8683 23 **Multiple-step process window aware OPC for hyper-NA lithography** [8683-73]
C. T. Hsuan, C. M. Hu, F. Lo, E. Yang, T. H. Yang, K. C. Chen, C.-Y. Lu, Macronix International Co., Ltd. (Taiwan)
- 8683 24 **Studies of a suitable mask error enhancement factor for 2D patterns** [8683-74]
C. I. Wei, Y. F. Cheng, M. J. Chen, United Microelectronics Corp. (Taiwan)
- 8683 25 **Pixel-based inverse lithography using a mask filtering technique** [8683-75]
W. Lv, Q. Xia, S. Liu, Huazhong Univ. of Science and Technology (China)
- 8683 26 **Imaging quality full chip verification for yield improvement** [8683-76]
Q. Yang, C. S. Zhou, S. F. Quek, M. Lu, Y. M. Foong, GLOBALFOUNDRIES Inc. (Singapore); J. H. Qiu, T. Pandey, R. Dover, ASML Brion Technologies (United States)
- 8683 27 **Hybrid OPC technique using model based and rule-based flows** [8683-77]
M. Harb, H. Abdelghany, Mentor Graphics Egypt (Egypt)
- 8683 29 **Model of freeform illumination mode and polarization mode for 193nm immersion lithographic machine** [8683-80]
Y. Zhang, A. Zeng, Y. Wang, M. Chen, H. Huang, Shanghai Institute of Optics and Fine Mechanics (China)
- 8683 2A **Analytical equation predicting the forbidden pattern pitch for phase-shifting mask** [8683-81]
J. Tamaki, Tokyo Polytechnic Univ. (Japan) and Orc Manufacturing Co., Ltd. (Japan); M. Shibuya, N. Suezou, Tokyo Polytechnic Univ. (Japan)
- 8683 2C **Optomechanical characterization of large wafer stepper-optics with respect to centering errors, lens distances, and center thicknesses** [8683-83]
D. Stickler, P. Langehanenberg, B. Lüerß, J. Heinisch, TRIOPTICS GmbH (Germany)
- 8683 2D **A customized Exicor system for measuring residual birefringence in lithographic lenses** [8683-84]
A. Breninger, B. Wang, Hinds Instruments, Inc. (United States)
- 8683 2E **Flare management for 40-nm logic devices** [8683-85]
Y. Tanaka, T. Tamura, M. Fujimoto, K. Tsubata, N. Onoda, K. Fujii, Renesas Electronics Corp. (Japan)
- 8683 2F **Wavefront testing of pinhole based on point diffraction interferometer** [8683-86]
X. Jin, T. Xing, J. Xu, W. Lin, Z. Liao, Institute of Optics and Electronics (China)

- 8683 2G **Design and simulation of illuminator with micro scanning slit array for NA 0.75 lithography system** [8683-87]
L. Zhu, Shanghai Institute of Optics and Fine Mechanics (China); A. Zeng, Shanghai Institute of Optics and Fine Mechanics (China) and Univ. of the Chinese Academy of Sciences (China); S. Zhang, Shanghai Institute of Optics and Fine Mechanics (China); R. Fang, H. Huang, Shanghai Institute of Optics and Fine Mechanics (China) and Univ. of the Chinese Academy of Sciences (China)
- 8683 2H **Zero expansion glass ceramic ZERODUR® roadmap for advanced lithography** [8683-88]
T. Westerhoff, R. Jedamzik, P. Hartmann, SCHOTT AG (Germany)
- 8683 2I **Mask side wall clamping** [8683-89]
G. J. P. Naaijkens, P. C. J. N. Rosielle, M. Steinbuch, Technische Univ. Eindhoven (Netherlands)

Author Index

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Bruce W. Smith, Rochester Institute of Technology (United States)

Kazuhiro Takahashi, Canon Inc. (Japan)

Geert Vandenberghe, IMEC (Belgium)

Session Chairs

- 1 Keynote Session
Will Conley, Cymer, Inc. (United States)
Kafai Lai, IBM Corporation (United States)
- 2 14nm and Beyond
Jongwook Kye, GLOBALFOUNDRIES Inc. (United States)
Tsai-Sheng Gau, Taiwan Semiconductor Manufacturing Company Ltd. (Taiwan)
- 3 Source and Mask Optimization (SMO) I
Andreas Erdmann, Fraunhofer-Institut für Integrierte Systeme und Bauelementetechnologie (Germany)
Bruce W. Smith, Rochester Institute of Technology (United States)
- 4 RET
Carlos Fonseca, Tokyo Electron America, Inc. (United States)
Sachiko Kobayashi, Toshiba Materials Company, Ltd. (Japan)
- 5 Source and Mask Optimization (SMO) II
Kazuhiro Takahashi, Canon Inc. (Japan)
Kurt Ronsed, IMEC (Belgium)
- 6 Process Technology I
Pary Baluswamy, Micron Technology, Inc. (United States)
Wilhelm Maurer, Infineon Technologies AG (Germany)
- 7 Modeling
Bernd Geh, Carl Zeiss SMT Inc. (United States)
Xuelong Shi, Semiconductor Manufacturing International Corporation (China)
- 8 Process Technology II
Sukjoo Lee, Samsung Electronics Company, Ltd. (Korea, Republic of)
Nigel R. Farrar, Cymer, Inc. (United States)
- 9 Optical and DFM I: Joint Session with Conferences 8683 and 8684
Mark E. Mason, Texas Instruments Inc. (United States)
Will Conley, Cymer, Inc. (United States)
- 10 Optical and DFM II: Joint Session with Conferences 8683 and 8684
Kafai Lai, IBM Corporation (United States)
John L. Sturtevant, Mentor Graphics Corporation (United States)

11 Simulation

Peter D. Brooker, Synopsys, Inc. (United States)

Yuri Granik, Mentor Graphics Corporation (United States)

12 Tooling

Soichi Owa, Nikon Corporation (Japan)

Jo Finders, ASML Netherlands B.V. (Netherlands)